SiE822DF

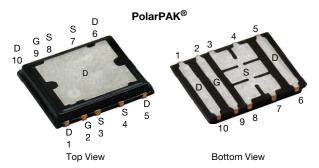
RoHS

COMPLIANT HALOGEN

FREE

Www.vishay.com

N-Channel 20 V (D-S) MOSFET



Top surface is connected to pins 1, 5, 6, and 10

PRODUCT SUMMARY						
V _{DS} (V)	20					
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.0034					
$R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V	0.0055					
Q _g typ. (nC)	24					
I _D (A) ^a (package limit)	50					
I _D (A) ^a (silicon limit)	138					
Configuration	Single					

FEATURES

- TrenchFET[®] power MOSFET
- Ultra low thermal resistance using top-exposed PolarPAK[®] package for double-sided cooling
- Leadframe-based encapsulated package
 Die not exposed
 Same layout regardless of die size
- Low Q_{ad}/Q_{as} ratio helps prevent shoot-through
- 100 % R_{α} and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- VRM
- DC/DC conversion
- Synchronous rectification



N-Channel MOSFET

ORDERING INFORMATION

Package	PolarPAK			
Lead (Pb)-free	SiE822DF-T1-E3			
Lead (Pb)-free and halogen-free	SiE822DF-T1-GE3			

ABSOLUTE MAXIMUM RATING	iS (T _A = 25 °C, ι	Inless otherwise	noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	20	v	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current (T _J = 150 °C)	T _ 25 °C		50 ^a (package limit)		
	T _C = 25 °C		138 (silicon limit)		
	T _C = 70 °C	I _D	50 ^a		
	T _A = 25 °C		31 ^{b, c}		
	T _A = 70 °C	1	24.8 ^{b, c}	A	
Pulsed drain current		I _{DM}	80		
	T _C = 25 °C		50 ^a		
Continuous source-drain diode current	T _A = 25 °C	I _S	4.3 ^{b, c}		
Single pulse avalanche current L = 0.1 mH		I _{AS}	30		
		E _{AS}	45	mJ	
	T _C = 25 °C		104	W	
Maximum power dissipation	T _C = 70 °C		66		
	T _A = 25 °C	P _D	5.2 ^{b, c}		
	T _A = 70 °C	1	3.3 ^{b, c}		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	*0	
Soldering recommendations (peak temperature) d, e		Ĭ	260		

Notes

a. Package limited is 50 A

b. Surface mounted on 1" x 1" FR4 board

c. t = 10 s

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PolarPAK is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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SiE822DF

Vishay Siliconix

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient a, b	$t \le 10 s$	R _{thJA}	20	24		
Maximum junction-to-case (drain top) ^a	Steady state	R _{thJC} (drain)	1	1.2	°C/W	
Maximum junction-to-case (source) a, c	Sleady State	R _{thJC} (source)	2.8	3.4		

Notes

a. Surface mounted on 1" x 1" FR4 board

b. Maximum under steady state conditions is 68 °C/W

c. Measured at source pin (on the side of the package)

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	20	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_J$	I _D = 250 μA	-	24.1	-	mV/°C	
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	ID = 230 μA	-	-7.1	-		
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	1.5	2.3	3.0	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$	-	-	± 100	nA	
Zoro gato voltago drain ourrant		$V_{DS} = 20 V, V_{GS} = 0 V$	-	-	1	μA	
Zero gate voltage drain current	IDSS	V_{DS} = 20 V, V_{GS} = 0 V, T_{J} = 55 °C	-	-	10		
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	25	-	-	А	
Drain-source on-state resistance ^a	_	V _{GS} = 10 V, I _D = 18.3 A	-	0.0028	0.0034	Ω	
Drain-source on-state resistance -	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 14.5 \text{ A}$	-	0.0045	0.0055	52	
Forward transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 18.3 A	-	90	-	S	
Dynamic ^b	· · ·						
Input capacitance	C _{iss}		-	4200	-		
Output capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	1000	-	pF	
Reverse transfer capacitance	C _{rss}		-	320	-		
Total gate charge		$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$	-	52	78	nC	
	Qg		-	24	36		
Gate-source charge	Q _{gs}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	13	-		
Gate-drain charge	Q _{gd}		-	5	-		
Gate resistance	R _g	f = 1 MHz	-	1	1.5	Ω	
Turn-on delay time	t _{d(on)}		-	50	75		
Rise time	t _r	$V_{DD} = 10 \text{ V}, \text{ R}_{L} = 1 \Omega,$	-	220	330	-	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	35	55		
Fall time	t _f		-	20	30		
Turn-on delay time	t _{d(on)}		-	15	25	ns	
Rise time	t _r	$V_{DD} = 20 V, R_{L} = 1 \Omega,$	-	25	40	-	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	35	55		
Fall time	t _f	-	-	10	15		
Drain-Source Body Diode Characterist							
Continuous source-drain diode current	IS	T _C = 25 °C	-	-	50		
Pulse diode forward current ^a	I _{SM}		-	-	80	A	
Body diode voltage	V _{SD}	I _S = 10 A	-	0.8	1.2	V	
Body diode reverse recovery time	t _{rr}	-	-	40	60	ns	
Body diode reverse recovery charge	Q _{rr}	I _F = 10 A, di/dt = 100 A/μs,	-	36	60	nC	
Reverse recovery fall time	ta	$T_{\rm J} = 25 ^{\circ}{\rm C}$	-	19	-		
Reverse recovery rise time	t _b	-	-	21	_	ns	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

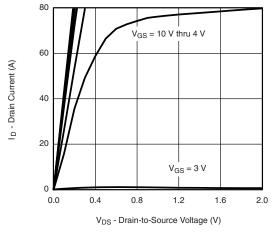
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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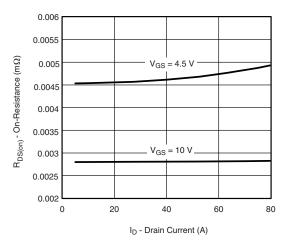
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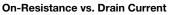


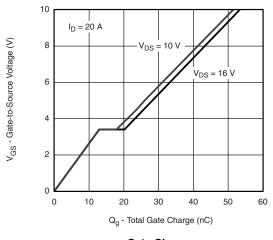
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



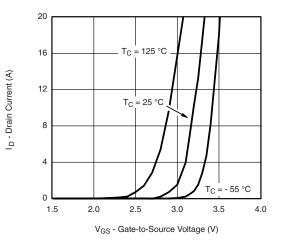




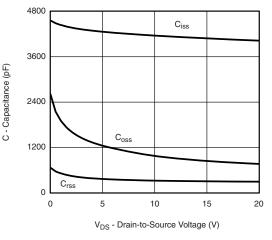




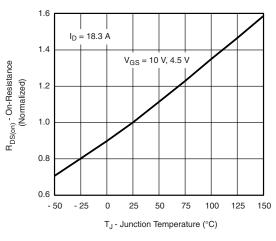
Gate Charge



Transfer Characteristics







On-Resistance vs. Junction Temperature

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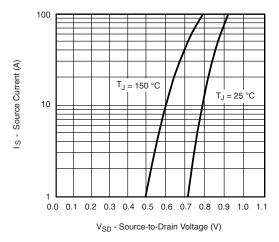
Document Number: 74451



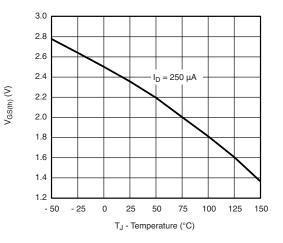
SiE822DF

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



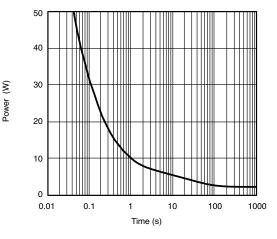
Source-Drain Diode Forward Voltage



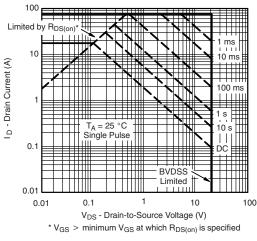


0.008 $R_{DS(on)}$ - Drain-to-Source On-Resistance ($\Omega)$ I_D = 18.3 A 0.007 0.006 0.005 T_A = 125 °C 0.004 $T_A = 25 \ ^\circ C$ 0.003 0.002 2 4 6 8 10 V_{GS} - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

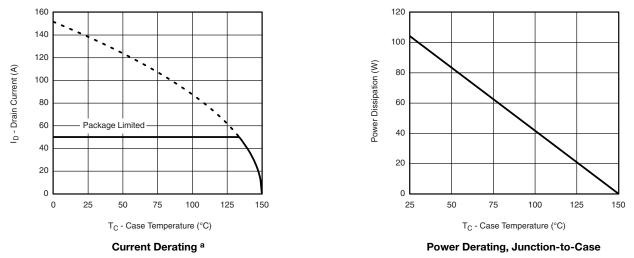
4



SiE822DF

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

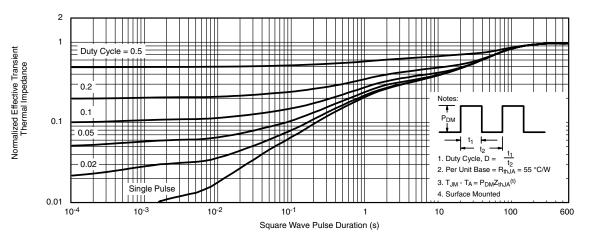


Note

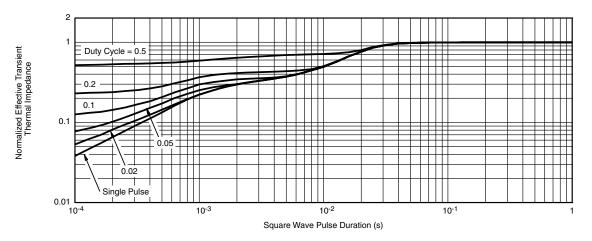
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



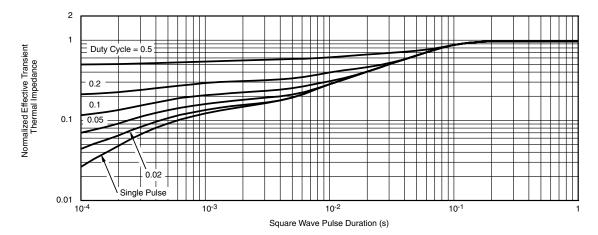
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case (Drain Top)



Normalized Thermal Transient Impedance, Junction-to-Source

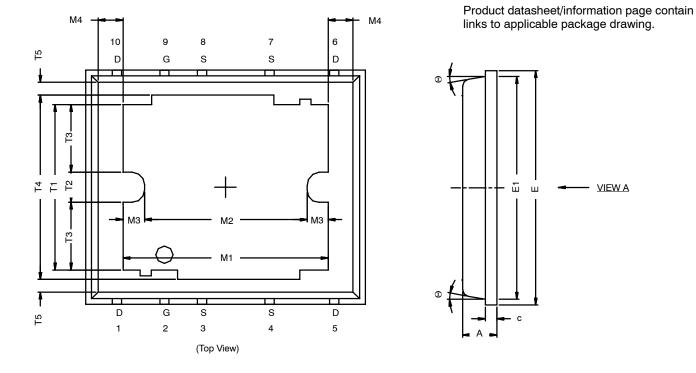
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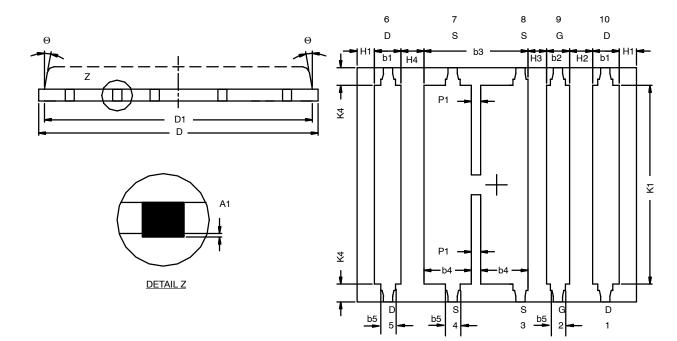
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Package Information Vishay Siliconix

PolarPAK[™] (Option S)





<u>VIEW A</u> (Bottom View)

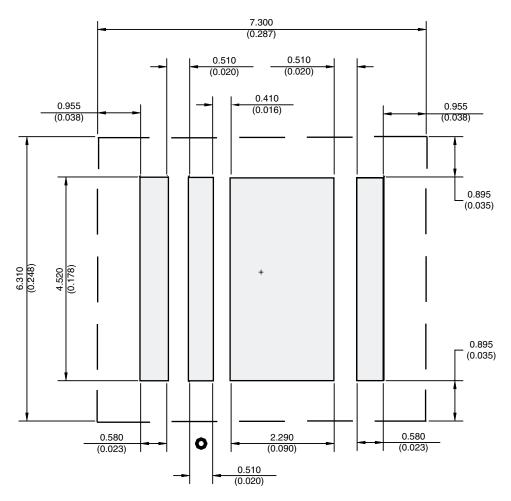


	MI	MILLIMETERS			INCHES	5
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.75	0.80	0.85	0.030	0.031	0.033
A1	0.00	-	0.05	0.000	-	0.002
b1	0.48	0.58	0.68	0.019	0.023	0.027
b2	0.41	0.51	0.61	0.016	0.020	0.024
b3	2.19	2.29	2.39	0.086	0.090	0.094
b4	0.89	1.04	1.19	0.035	0.041	0.047
b5	0.23	0.33	0.43	0.009	0.013	0.017
С	0.20	0.25	0.30	0.008	0.010	0.012
D	6.00	6.15	6.30	0.236	0.242	0.248
D1	5.74	5.89	6.04	0.226	0.232	0.238
Е	5.01	5.16	5.31	0.197	0.203	0.209
E1	4.75	4.90	5.05	0.187	0.193	0.199
H1	0.23	-	-	0.009	-	-
H2	0.45	-	0.56	0.020	-	0.022
H3	0.31	0.41	0.51	0.012	0.016	0.020
H4	0.45	-	0.56	0.020	-	0.022
K1	4.22	4.37	4.52	0.166	0.172	0.178
K4	0.24	-	-	0.009	-	-
M1	4.30	4.50	4.70	0.169	0.177	0.185
M2	3.43	3.58	3.73	0.135	0.141	0.147
M3	0.22	-	-	0.009	-	-
M4	0.05	-	-	0.002	-	-
P1	0.15	0.20	0.25	0.006	0.008	0.010
T1	3.48	3.64	4.10	0.137	0.143	0.150
T2	0.56	0.76	0.95	0.22	0.030	0.037
Т3	1.20	-	-	0.051	-	-
T4	3.90	-	-	0.154	-	-
T5	0	0.18	0.36	0.000	0.007	0.014
Θ	0°	10°	12°	0°	10°	12°

Note: Millimeters govern over inches



RECOMMENDED MINIMUM PADS FOR PolarPAK® Option L and S



Recommended Minimum for PolarPAK Option L and S Dimensions in mm/(Inches) No External Traces within Broken Lines Dot indicates Gate Pin (Part Marking)

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